

# GOODRAM Industrial CFExpress Memory Card 3D TLC type

DATASHEET

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CFExpress Card for Industrial Applications

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### **REVISION HISTORY**

| VERSION | CHANGES         | DATE       |
|---------|-----------------|------------|
| 1.0     | Initial release | 08.08.2022 |



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### **PRODUCT OVERVIEW**

- Capacity:
  - o 15GB, 30GB, 60GB, 120GB, 240GB, 480GB
  - Flash Type

     3D TLC Kioxia BiCS Flash
  - Host Interface o Gen3 x2 Lanes
  - Type B CFExpress
  - Performance <sup>Note1</sup> Sequential Read: Up to 1610 MB/s
    Sequential Write: Up to 820 MB/s
  - Power Consumption <sup>Note2</sup> • Idle mode: < 102mW
  - RoHS compliant
  - REACH compliant
  - Host Memory Buffer

**MTBF** ○ More than 2 000 000 hours

#### Endurance

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O Up to 3 000 erase/program
 O Data retention 10 years in room temperature (40°C)<sup>Note3</sup>

#### • Advanced Flash Management

- o Static and Dynamic Wear Levelling
- o LDPC ECC
- o Subpage Mode Flash Translation Layer
- o Data Care Management
- o Lifetime Enhancements
- o Power Fail Data Loss Protection
- o TRIM
- o Active State Power Management
- o Firmware Update
- o S.M.A.R.T
- o TCG Opal (on demand)
- End-to-End Data Protection
- o AES256 Encryption (on demand, active for 480GB)
- Low Power Management
  - $\circ\,$  Power Sleep Mode
- Temperature Range
  - Operation: -40 ~ +85°C
     Storage: -40 ~ +85°C

#### Notes:

- 1. Measured by CrystalDiskMark v3.0
- 2. Please see "Power Consumption" for details.
- 3. In new product.



### **PRODUCT DETAILS**

#### **GENERAL DESCRIPTION**

CFExpress<sup>™</sup> cards are currently the newest solution supported by Compact Flash Association, which is capable of to fulfill the most rigid demands of industrial customer. By offering excellent performance and wide compatibility, GOODRAM's CFExpress<sup>™</sup> Card also provides a wide range of capacities available for users. In addition, industrial-grade CFExpress<sup>™</sup> cards are available for any applications under rigorous environmental conditions including extensive temperature, shock and vibration.

#### MAIN FLASH MANAGEMENT TOOLS

GOODRAM CFExpress<sup>™</sup> card utilizes all the state of art technologies to ensure full reliability until the specified NAND Flash program/erase cycles parameter is reached. These technologies include but are not limited to:

#### Error Correction Code (ECC)

Flash memory cells will deteriorate with use, which might generate random bit errors in the stored data. Thus, CFExpress<sup>™</sup> controller applies the LDPC ECC algorithm, which can detect and correct errors occur during read process, ensure data been read correctly, as well as protect data from corruption.

#### Wear Levelling

NAND Flash devices can only undergo a limited number of program/erase cycles, and in most cases, the flash media are not used evenly. If some area get updated more frequently than others, the lifetime of the device would be reduced significantly. Thus, Wear Leveling technique is applied to extend the lifespan of NAND Flash by evenly distributing write and erase cycles across the media. Product has advanced Wear Leveling algorithm, which can efficiently spread out the flash usage through the whole flash media area. Moreover, by implementing both dynamic and static Wear Leveling algorithms, the life expectancy of the NAND Flash is greatly improved.

#### **Bad Block Management**

Bad blocks are blocks that include one or more invalid bits, and their reliability is not guaranteed. Blocks that are identified and marked as bad by the manufacturer are referred to as "Initial Bad Blocks". Bad blocks that are developed during the lifespan of the flash are named "Later Bad Blocks". We implement an efficient bad block management algorithm to detect the factory-produced bad blocks and manages any bad blocks that appear with use. This practice further prevents data being stored into bad blocks and improves the data reliability.



#### Firmware Upgrade

Firmware can be considered as a set of instructions on how the device communicates with the host. Firmware will be upgraded when new features are added, compatibility issues are fixed or read/write performance gets improved.

#### ADDITIONAL FEATURES

#### **Power Management**

Active State Power Management (ASPM) is a power management mechanism for PCIe devices to reduce power consumption while running. This is achieved through powering down the PCIe serial link when there is no traffic across it.

### PERFORMANCE AND POWER CONSUMPTION

|          |                    | Performance<br>Sequential Read/Write |                              |                           | Power Consumption          |              |               |              |
|----------|--------------------|--------------------------------------|------------------------------|---------------------------|----------------------------|--------------|---------------|--------------|
| Capacity | Flash<br>Structure | Read HMB<br>on<br>(MB/s)             | Read<br>HMB<br>off<br>(MB/s) | Write<br>HMB on<br>(MB/s) | Write<br>HMB off<br>(MB/s) | Read<br>(mW) | Write<br>(mW) | Idle<br>(mW) |
| 15GB     | 1x128Gb            | 290                                  | 290                          | 100                       | 60                         | 380          | 360           | 102          |
| 30GB     | 1x256Gb            | 290                                  | 290                          | 100                       | 60                         | 380          | 360           | 102          |
| 60GB     | 2x256Gb            | 590                                  | 580                          | 200                       | 150                        | 460          | 410           | 102          |
| 120GB    | 4x256Gb            | 1 180                                | 1 1 4 0                      | 380                       | 200                        | 610          | 480           | 102          |
| 240GB    | 8x256Gb            | 1 610                                | 1 590                        | 700                       | 370                        | 690          | 590           | 102          |
| 480GB    | 8x512Gb            | 1 610                                | 1 600                        | 820                       | 580                        | 760          | 700           | 102          |

#### NOTES:

1. The performance was measured using CrystalDiskMark 7.0.0.

2. All values are typical total values recorded at 25 °C

3. HMB – Host Memory Buffer.

4. The table above is for reference only. The criteria for MP (mass production) and for accepting goods shall be discussed based on different flash configuration.



### SUPPLY VOLTAGE

| Parameter                  | Symbol | Min | TYP | MAX | Unit |
|----------------------------|--------|-----|-----|-----|------|
| V <sub>DD</sub><br>Voltage | VDD    | 3.1 | 3.3 | 3.5 | V    |

# Temperature specification

| SYMBOL          | PARAMETER                     | MIN. | MAX. | UNIT |
|-----------------|-------------------------------|------|------|------|
| Ta              | Operating Temperature Diamond | -40  | +85  | °C   |
| T <sub>st</sub> | Storage Temperature           | -40  | +85  | °C   |

### TBW

| Capacity | Flash Structure | TBW Sequential |
|----------|-----------------|----------------|
| 15GB     | 1x128Gb         | 24             |
| 30GB     | 1x256Gb         | 51             |
| 60GB     | 2x256Gb         | 107            |
| 120GB    | 4x256Gb         | 218            |
| 240GB    | 8x256Gb         | 444            |
| 480GB    | 8x512Gb         | 1 420          |

NOTES:

1. The test followed JEDEC219 client endurance workload.

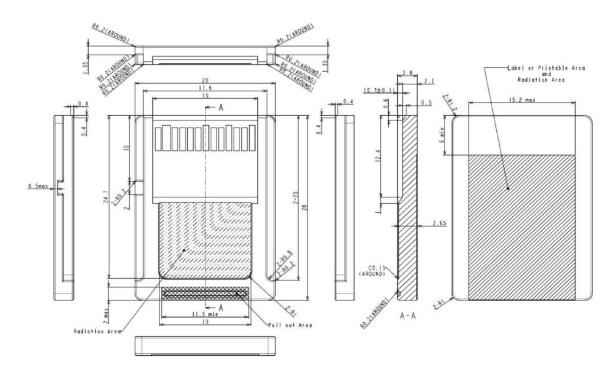
2. TBW may differ according to flash configuration and platform.

3. The endurance of CFExpress could be estimated based on user behaviour, NAND endurance cycles, and write amplification factor. It is not guaranteed by flash vendor.



### **PHYSICAL DIMENSION**

Dimension: 38.5 ± 0,20 mm (L) x 29.6 ± 0,10 mm (W) x 3.80 ± 0,10 mm (H)





# **PIN ASSIGNMENT AND DESCRIPTIONS**

| Pin No. | Signal   | I/O | Host | Notes |
|---------|----------|-----|------|-------|
| 1       | GND      |     | R    |       |
| 2       | PERp1    | 0   | Opt  |       |
| 3       | PERn1    | 0   | Opt  |       |
| 4       | GND      |     | Opt  | 3     |
| 5       | PETn1    |     | Opt  |       |
| 6       | PETp1    |     | Opt  |       |
| 7       | Reserved |     | NC   |       |
| 8       | Reserved |     | NC   |       |
| 9       | PERST#   |     | R    |       |
| 10      | +3.3V    |     | R    |       |
| 11      | CLKREQ#  | 0   | Opt  | 2     |
| 12      | INS#     | 0   | R    | 1     |
| 13      | REFCLK-  |     | R    |       |
| 14      | REFCLK+  |     | R    |       |
| 15      | GND      |     | R    |       |
| 16      | PERn0    | 0   | R    |       |
| 17      | PERp0    | 0   | R    |       |
| 18      | GND      |     | R    |       |
| 19      | PETn0    |     | R    |       |
| 20      | PETp0    |     | R    |       |
| 21      | GND      |     | R    |       |

Notes:

1. A host pull-up resistor in the range of  $100k\Omega$ - $200k\Omega$  is required on this pin. This pin is internally strapped to the ground.

2. A host pull-up resistor  $(\geq 5k\Omega)$  is required on this pin.

3. In case that PCI Express Transmitter differential pair Lane 1 and Receiver differential pair Lane 1 are implemented, pin 4 shall be connected to ground.

# SUPPORTED NVMe COMMAND LIST

| Command                     | Code | Command          | Code |
|-----------------------------|------|------------------|------|
| Delete I/0 Submission Queue | 00h  | Create I/0 Queue | 01h  |
| Get Log Page                | 02h  | Delete I/O       | 04h  |
|                             |      | Completion Queue |      |
| Create I/O Completion Queue | 05h  | Identify         | 06h  |
| Abort                       | 08h  | Set Features     | 09h  |
| Get Features                | 0Ah  | Asynchronous     | 0Ch  |
|                             |      | Event Request    |      |



| Firmware Commit    | 10h | Firmware Image<br>Download | 11h |
|--------------------|-----|----------------------------|-----|
| Device Self-test   | 14h | Format NVM                 | 80h |
| Sanitize           | 84h |                            |     |
| NVM Command Set    |     |                            |     |
| Flush              | 00h | Write                      | 01h |
| Read               | 02h | Write Uncorrectable        | 04h |
| Compare            | 05h | Write Zeroes               | 08h |
| Dataset Management | 09h |                            |     |

# **PRODUCT ORDERING INFORMATION**

| PN                  | Туре      | Capacity | Technology | Temp range |
|---------------------|-----------|----------|------------|------------|
| CFEXB-0153DG-S03KID | CFExpress | 15 GB    | 3D TLC     | -40 ~85°C  |
| CFEXB-0303DG-S03KID | CFExpress | 30 GB    | 3D TLC     | -40~85°C   |
| CFEXB-0603DG-S03KID | CFExpress | 60 GB    | 3D TLC     | -40 ~85°C  |
| CFEXB-1203DG-S03KID | CFExpress | 120 GB   | 3D TLC     | -40 ~85°C  |
| CFEXB-2403DG-S03KID | CFExpress | 240 GB   | 3D TLC     | -40 ~85°C  |
| CFEXB-4803DG-S03KIE | CFExpress | 480 GB   | 3D TLC     | -40 ~85°C  |



### **STANDARDS & REFERENCES**

The following table is to list out the standards that have been adopted for designing the product.

| STANDARD USED                | ACRONYM/SOURCE   |
|------------------------------|--|
| RoHS                         | Restriction of Hazardous Substances Directive; please contact us for further information |
| CompactFlash™ Card           | http://www.compactflash.org/   |
| PC Card Standard Release 8.0 | http://www.compactflash.org/   |
| CE                           | Consumer electronics certification; please contact us for further information.           |

# SAFETY PRECAUTIONS

Do not bend, crush, drop, or place heavy objects on top of the Product. Do not use tweezers, pliers or similar items that could damage the Product. Take particular care when inserting or removing the Product. Stop using the Product when the Product does not work properly. Failure to follow these instructions could result in fire, damage to the Product and/or other property, and/or personal injury including burns and electric shock.

Keep out of reach of small children. Accidental swallowing may cause suffocation or injury. Contact a doctor immediately if you suspect a child has swallowed the Product.

Do not directly touch the interface pins, put them in contact with metal, strike them with hard objects or cause them to short. Do not expose to static electricity.

Do not disassemble or modify the Product. This may cause electric shock, damage to the Product or fire.



#### **NOTES ON USAGE**

The Product contains nonvolatile semiconductor memory. Do not use the Product in accordance with a method of usage other than that written in the manual. This may cause the destruction or loss of data.

To protect against accidental data loss, you should back up your data frequently on more than one type of storage media. Wilk Elektronik S.A. assumes no liability for destruction or loss of data recorded on the Card for any reason.

When used over a long period of time or repeatedly, the reading, writing and deleting capabilities of the Product will eventually fail, and the performance speed of the Product may decrease below the original speed specific to the Product's applicable class.

If the Product is to be transferred or destroyed, note that the data it contained may still be recoverable unless it is permanently deleted by third-party deletion software or similar means beforehand.

Product is intended for use in general electronics applications and selected industrial applications and any other specific applications as expressly stated in this document. Product is neither intended nor warranted for use in equipment or systems where failure may cause loss of human life, bodily injury, serious property damage or serious public impact ("Unintended Use"). Unintended Use includes, without limitation, equipment used in nuclear facilities, equipment used in the aerospace industry, medical equipment or equipment used to control combustions or explosions. Do not use Product for Unintended Use unless specifically permitted in this document.

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